

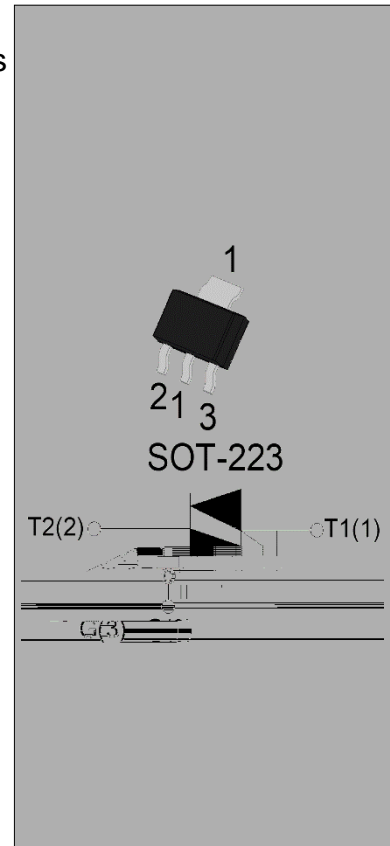


JPTT01V-800SW 1A TRIAC

Rev.A.1.2

DESCRIPTION:

The JPTT01V-800SW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. The JPTT01V-800SW embeds a TVS structure to absorb the inductive turn-off energy such as those described in the IEC 61000-4-5 standards. At the same time, the triac shields the positive signal trigger to reduce the probability of product misoperation. It is triggered with a negative gate current flowing out of the gate pin. Package SOT-223 is RoHS compliant.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	1	A
V_{DRM}/V_{RRM}	800	V
I_{GT} /	10/10	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ C$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ C$)	V_{RRM}	800	V
RMS on-state current ($T_c = 106^\circ C$)	$I_{T(RMS)}$	1	A
Non repetitive surge peak on-state current (full cycle, $t_p=20ms$, $T_j=25^\circ C$)	I_{TSM}	14	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6ms$, $T_j=25^\circ C$)		15.4	
I^2t value for fusing ($t_p=10ms$, $T_j=25^\circ C$)	I^2t	0.98	A^2s
Critical rate of rise of on-state current ($I_G=2 I_{GT}$, $f=100Hz$, $T_j=125^\circ C$)	di/dt	100	$A/\mu s$
Peak gate current ($t_p=20\mu s$, $T_j=125^\circ C$)	I_{GM}	1	A
Positive applied gate voltage	V_{GM}	15	V

Average gate power dissipation ($T_j=125$)	$P_{G(AV)}$	0.1	W
Peak gate power	P_{GM}	2	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.8)	V_{pp}	2.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V R_L=33$	-	MAX.	10	mA
V_{GT}		-	MAX.	1.3	V
V_{GD}	$V_D=V_{DRM} T_j=125$ $R_L=3.3K$	-	MIN.	0.15	V
I_L	$I_G=1.2I_{GT}$		MAX.	40	mA
				20	
I_H	$I_T=100mA$		MAX.	20	mA
dV/dt	$V_D=540V$ Gate Open $T_j=125$		MIN.	1000	V/ μs
(dI/dt) _c	(dV/dt) _c =15V/ μs , $T_j=125$		MIN.	2	A/ms
t_{on}	$I_G=20mA I_A=200mA I_R=20mA$ $T_j=25$		TYP.	2.5	μs
t_{off}				25	
V_{CL}	$I_{CL}=0.1mA t_p=1ms$		MIN.	950	V

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=1.1A t_p=380\mu s$	$T_j=25$	1.3	V
V_{TO}	Threshold voltage	$T_j=125$	0.8	V
R_D	Dynamic resistance	$T_j=125$	385	m
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$	2	μA
I_{RRM}		$T_j=125$	0.2	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	15	/W
$R_{th(j-a)}$	junction to ambient (AC, in free air, $S=5cm^2$)	55	/W

ORDERING INFORMATION

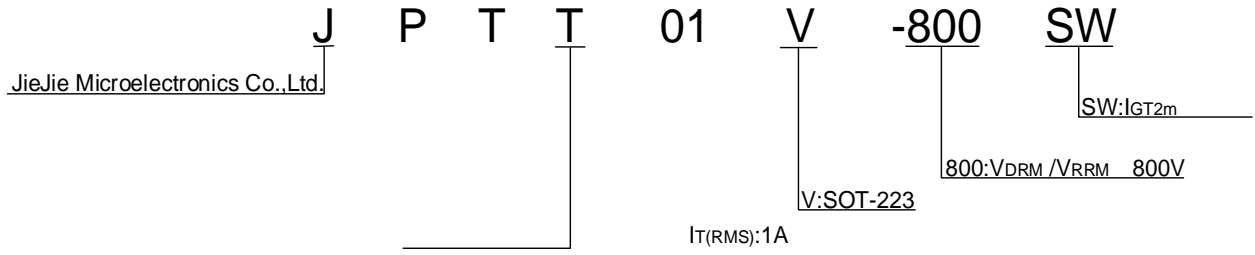


FIG.1 Maximum power dissipation versus RMS on-state current

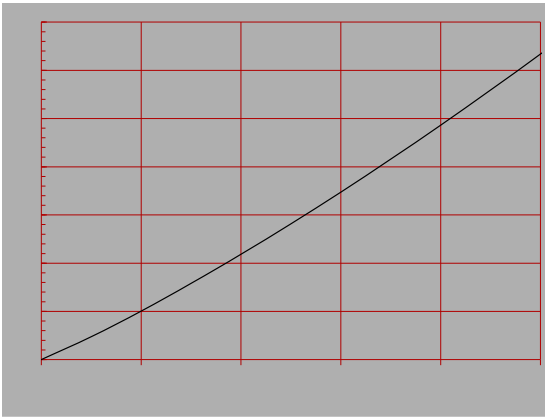


FIG.2: RMS on-state current versus case temperature

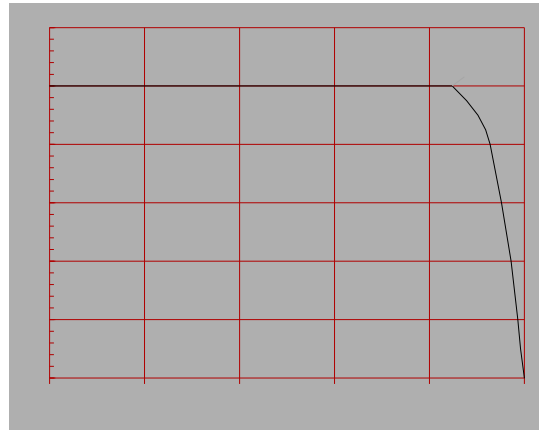


FIG.3: RMS on-state current versus ambient temperature (free air convection)

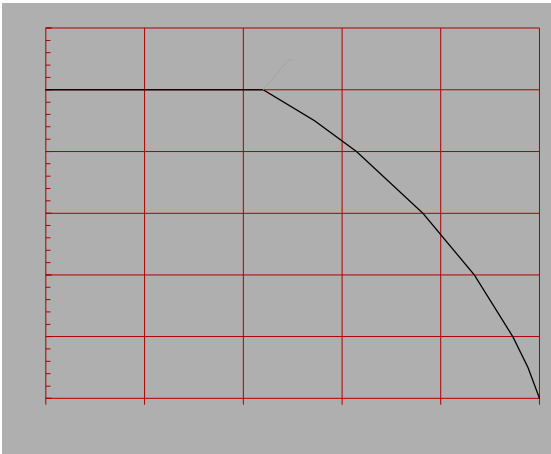


FIG.4: Surge peak on-state current versus number of cycles

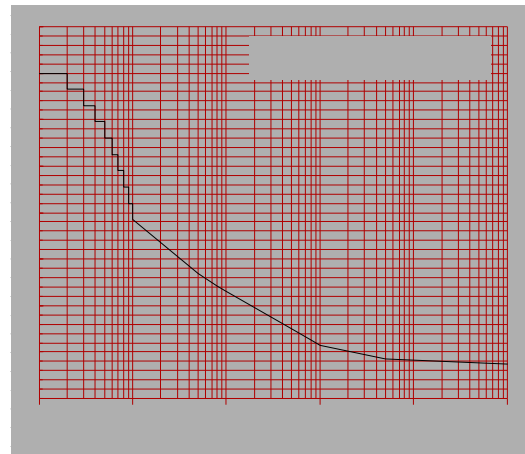


FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

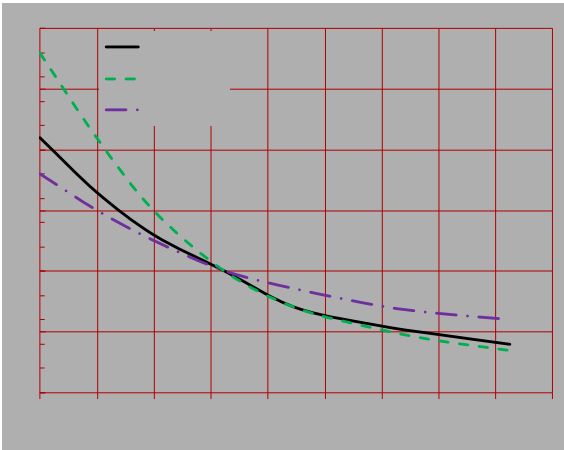
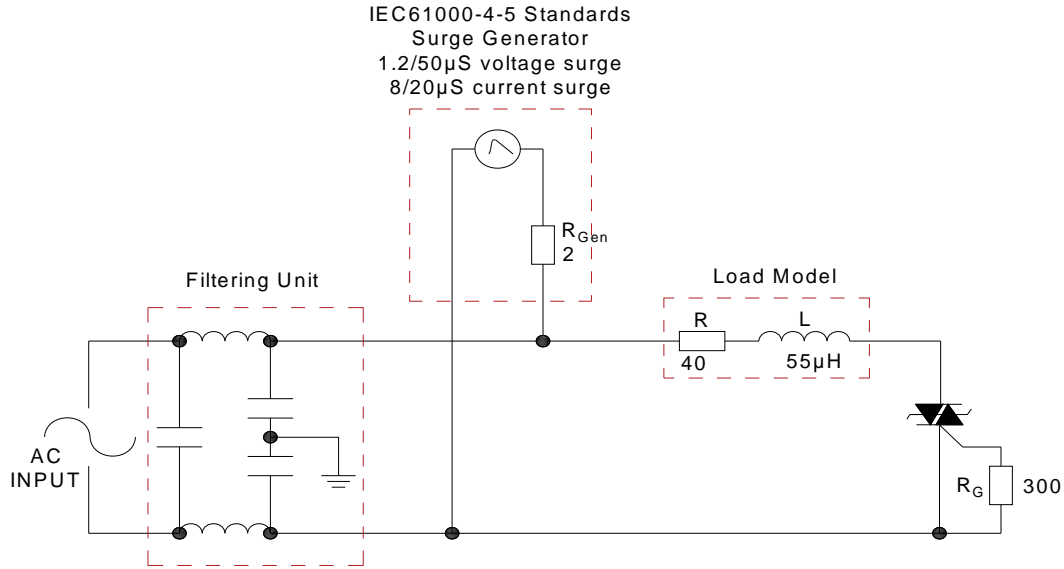
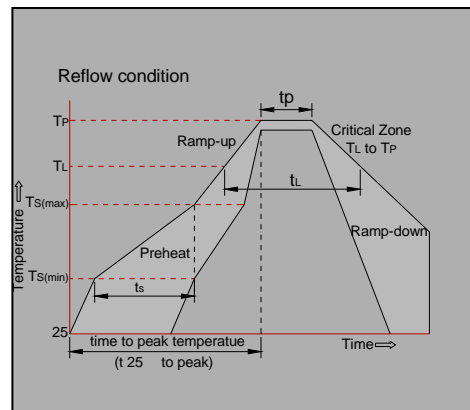


FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



SOLDERING PARAMETERS

Reflow Condition		Pb-Free assembly (see figure at right)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150
	-Temperature Max($T_{s(max)}$)	+200
	-Time (Min to Max) (t_s)	60-180 secs.
Average ramp up rate (Liquidus Temp (T_L) to peak)		3 /sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3 /sec. Max
Reflow	-Temperature(T_L)(Liquidus)	+217
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)
Time within 5 of actual Peak Temp (t_p)		20-40secs.
Ramp-down Rate		6 /sec. Max
Time 25 to Peak Temp (T_p)		8 min. Max
Do not exceed		+260



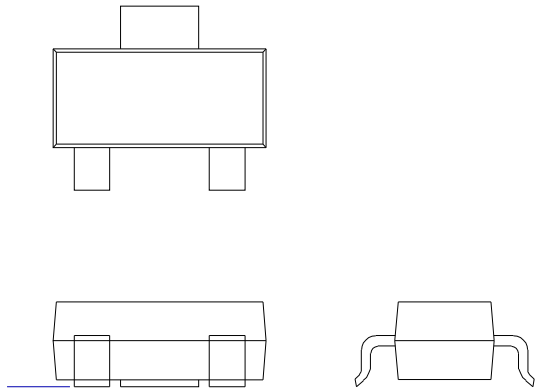
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JPTT01V-800SW	800	10	SOT-223	4,000	Tape & Reel

Document Revision History

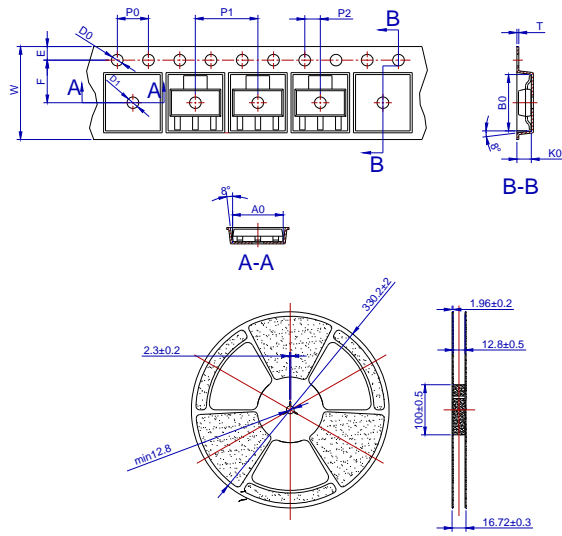
Date	Revision	Changes
Apr.10, 2023	A.1.0	Last updated
May.06, 2023	A.1.1	Renew (di/dt)c
Aug.07, 2024	A 1.2	Renew V_{TM} & $R_{th(j-a)}$ & FIG.1 & FIG.2 & FIG.3 & FIG.5 & FIG.6

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.5	1.6	1.8	0.059	0.063	0.071
A1	0.01	0.06	0.10	0.001	0.002	0.004
B	2.9	3.0	3.1	0.114	0.118	0.122
B1	0.6	0.7	0.8	0.024	0.028	0.031
C	0.22	0.26	0.32	0.009	0.010	0.013
D	6.3	6.5	6.7	0.248	0.256	0.264
E	3.3	3.5	3.7	0.130	0.138	0.146
F	4.4			0.173		
F1	2.2			0.087		
G	0.5		1.0	0.020		0.039
H	1.5	1.75	2.0	0.059	0.069	0.079
J	6.7	7.0	7.3	0.264	0.276	0.287
K		0.9			0.035	

DELIVERY MODE




Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	-	-	12.30	-	-	0.482
E	1.65	1.75	1.85	0.065	0.069	0.073
F	5.45	5.50	5.55	0.215	0.217	0.219
D0	1.50	1.55	1.60	0.059	0.061	0.063
D1	1.50	-	-	0.059	-	-
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.95	2.00	2.05	0.077	0.079	0.081
10P0	39.80	40.00	40.20	1.567	1.575	1.583
A0	6.85	6.95	7.05	0.269	0.273	0.276
B0	7.15	7.25	7.35	0.280	0.284	0.288
K0	1.95	2.05	2.15	0.076	0.080	0.084
T	0.20	0.25	0.30	0.008	0.010	0.012

PACKAGE	OUTLINE	REEL (PCS)	PER CARTON (PCS)	TAPE & REEL
SOT-223	TAPING	4,000	40,000	13 inch

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